

CNB1302

Reflective Photosensor

■ Overview

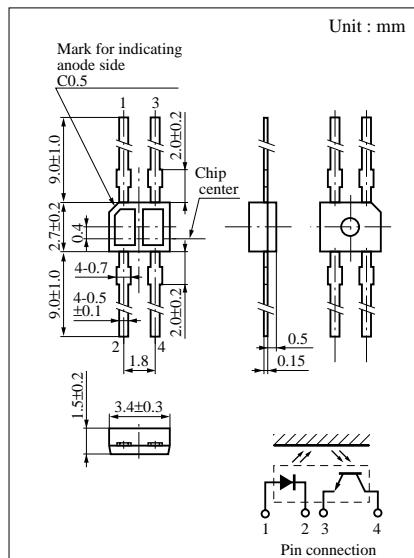
CNB1302 is a small, thin reflective photosensor consisting of a high efficiency GaAs infrared light emitting diode which is integrated with a high sensitivity Si phototransistor in a single resin package.

■ Features

- Ultraminiature, thin type : $2.7 \times 3.4 \text{ mm}$ (height : 1.5 mm)
- Visible light cutoff resin is used
- Fast response : $t_r, t_f = 20\mu\text{s}$ (typ.)
- Easy interface for control circuit

■ Applications

- Control of motor and other rotary units
- Detection of position and edge
- Detection of paper, film and cloth
- Start, end mark detection of magnetic tape



■ Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

| | Parameter | Symbol | Ratings | Unit |
|------------------------------|-------------------------------|------------|-------------|------|
| Input (Light emitting diode) | Reverse voltage (DC) | V_R | 3 | V |
| | Forward current (DC) | I_F | 50 | mA |
| | Power dissipation | P_D^{*1} | 75 | mW |
| Output (Photo transistor) | Collector current | I_C | 20 | mA |
| | Collector to emitter voltage | V_{CEO} | 30 | V |
| | Emitter to collector voltage | V_{ECO} | 5 | V |
| Temperature | Collector power dissipation | P_C^{*2} | 50 | mW |
| | Operating ambient temperature | T_{opr} | -25 to +85 | °C |
| | Storage temperature | T_{stg} | -30 to +100 | °C |

*¹ Input power derating ratio is
1.0 mW/°C at $T_a \geq 25^\circ\text{C}$.

*² Output power derating ratio is
0.67 mW/°C at $T_a \geq 25^\circ\text{C}$.

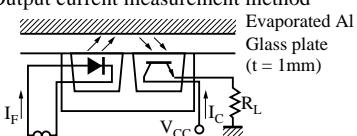
■ Electrical Characteristics ($T_a = 25^\circ\text{C}$)

| | Paramwter | Symbol | Conditions | min | typ | max | Unit |
|--------------------------|---|----------------------|--|-----|------|-----|------|
| Input characteristics | Forward voltage (DC) | V_F | $I_F = 50\text{mA}$ | | 1.3 | 1.5 | V |
| | Reverse current (DC) | I_R | $V_R = 3\text{V}$ | | 0.01 | 10 | µA |
| | Capacitance between terminals | C_t | $V_R = 0\text{V}, f = 1\text{MHz}$ | | 30 | | pF |
| Output characteristics | Collector cutoff current | I_{CEO} | $V_{CE} = 10\text{V}$ | | | 200 | nA |
| | Collector current | $I_C^{*1, *2}$ | $V_{CC} = 5\text{V}, I_F = 10\text{mA}, R_L = 100\Omega, d = 1\text{mm}$ | 90 | | 880 | µA |
| | Leakage current | I_D | $V_{CC} = 5\text{V}, I_F = 10\text{mA}, R_L = 100\Omega$ | | | 200 | nA |
| Transfer characteristics | Response time | t_r^{*3}, t_f^{*4} | $V_{CC} = 5\text{V}, I_C = 0.1\text{mA}, R_L = 100\Omega$ | | 20 | | µs |
| | Collector to emitter saturation voltage | $V_{CE(\text{sat})}$ | $I_F = 20\text{mA}, I_C = 0.1\text{mA}$ | | | 0.4 | V |

*¹ I_C classifications

| Class | Q | R | S |
|---------------------|-----------|------------|------------|
| $I_C (\mu\text{A})$ | 90 to 220 | 180 to 440 | 360 to 880 |

*² Output current measurement method



*³ Time required for the output current to increase from 10% to 90% of its final value

*⁴ Time required for the output current to decrease from 90% to 10% of its initial value

